



**AO7410**

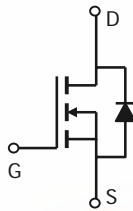
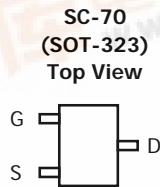
**N-Channel Enhancement Mode Field Effect Transistor**

**General Description**

The AO7410 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , very low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications. *Standard Product AO7410 is Pb-free (meets ROHS & Sony 259 specifications). AO7410L is a Green Product ordering option. AO7410 and AO7410L are electrically identical.*

**Features**

- $V_{DS}$  (V) = 30V
- $I_D$  = 1.6 A ( $V_{GS}$  = 10V)
- $R_{DS(ON)}$  < 90m $\Omega$  ( $V_{GS}$  = 10V)
- $R_{DS(ON)}$  < 100m $\Omega$  ( $V_{GS}$  = 4.5V)
- $R_{DS(ON)}$  < 175m $\Omega$  ( $V_{GS}$  = 2.5V)



**Absolute Maximum Ratings  $T_A=25^\circ\text{C}$  unless otherwise noted**

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	V
Continuous Drain Current <sup>A</sup>	$I_D$	$T_A=25^\circ\text{C}$	1.6
		$T_A=70^\circ\text{C}$	1.3
Pulsed Drain Current <sup>B</sup>	$I_{DM}$	10	A
Power Dissipation <sup>A</sup>	$P_D$	$T_A=25^\circ\text{C}$	0.35
		$T_A=70^\circ\text{C}$	0.22
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$

**Thermal Characteristics**

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	300	360	$^\circ\text{C}/\text{W}$
Maximum Junction-to-Ambient <sup>A</sup>		Steady-State	340	425
Maximum Junction-to-Lead <sup>C</sup>	$R_{\theta JL}$	280	320	$^\circ\text{C}/\text{W}$



Electrical Characteristics ( $T_J=25^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}$ , $V_{GS}=0\text{V}$	30			V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=24\text{V}$ , $V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$		0.001	1	$\mu\text{A}$
					5	
$I_{GSS}$	Gate-Body leakage current	$V_{DS}=0\text{V}$ , $V_{GS}=\pm 12\text{V}$			100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$ , $I_D=250\mu\text{A}$	1	1.4	1.8	V
$I_{D(ON)}$	On state drain current	$V_{GS}=4.5\text{V}$ , $V_{DS}=5\text{V}$	10			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}$ , $I_D=1.6\text{A}$ $T_J=125^\circ\text{C}$		75	90	m $\Omega$
				105	130	
			$V_{GS}=4.5\text{V}$ , $I_D=1.5\text{A}$		82	
		$V_{GS}=2.5\text{V}$ , $I_D=1\text{A}$		120	175	m $\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS}=5\text{V}$ , $I_D=3.8\text{A}$		4.5		S
$V_{SD}$	Diode Forward Voltage	$I_S=1\text{A}$ , $V_{GS}=0\text{V}$		0.84	1	V
$I_S$	Maximum Body-Diode Continuous Current				2.5	A
<b>DYNAMIC PARAMETERS</b>						
$C_{iss}$	Input Capacitance	$V_{GS}=0\text{V}$ , $V_{DS}=15\text{V}$ , $f=1\text{MHz}$		226	270	pF
$C_{oss}$	Output Capacitance			39		pF
$C_{rss}$	Reverse Transfer Capacitance			29		pF
$R_g$	Gate resistance	$V_{GS}=0\text{V}$ , $V_{DS}=0\text{V}$ , $f=1\text{MHz}$		1.4	1.7	$\Omega$
<b>SWITCHING PARAMETERS</b>						
$Q_g$	Total Gate Charge	$V_{GS}=4.5\text{V}$ , $V_{DS}=15\text{V}$ , $I_D=1.6\text{A}$		3	3.6	nC
$Q_{gs}$	Gate Source Charge			0.4		nC
$Q_{gd}$	Gate Drain Charge			1.2		nC
$t_{D(on)}$	Turn-On DelayTime	$V_{GS}=10\text{V}$ , $V_{DS}=15\text{V}$ , $R_L=9.4\Omega$ , $R_{GEN}=6\Omega$		2.8	4	ns
$t_r$	Turn-On Rise Time			2.1	3	ns
$t_{D(off)}$	Turn-Off DelayTime			17.4	21	ns
$t_f$	Turn-Off Fall Time			2.1	3	ns
$t_{rr}$	Body Diode Reverse Recovery Time	$I_F=1.6\text{A}$ , $dI/dt=100\text{A}/\mu\text{s}$		9.1	11	ns
$Q_{rr}$	Body Diode Reverse Recovery Charge	$I_F=1.6\text{A}$ , $dI/dt=100\text{A}/\mu\text{s}$		3.4	4	nC

A: The value of  $R_{\theta JA}$  is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The value in any given application depends on the user's specific board design. The current rating is based on the  $t \leq 10\text{s}$  thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The  $R_{\theta JA}$  is the sum of the thermal impedance from junction to lead  $R_{\theta JL}$  and lead to ambient.

D: The static characteristics in Figures 1 to 6,12,14 are obtained using 80 $\mu\text{s}$  pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

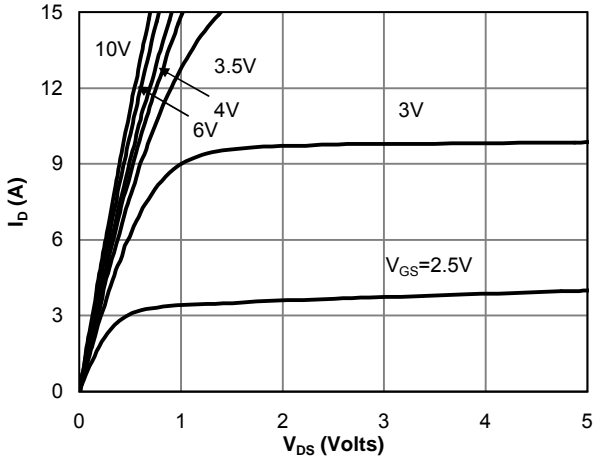


Fig 1: On-Region Characteristics

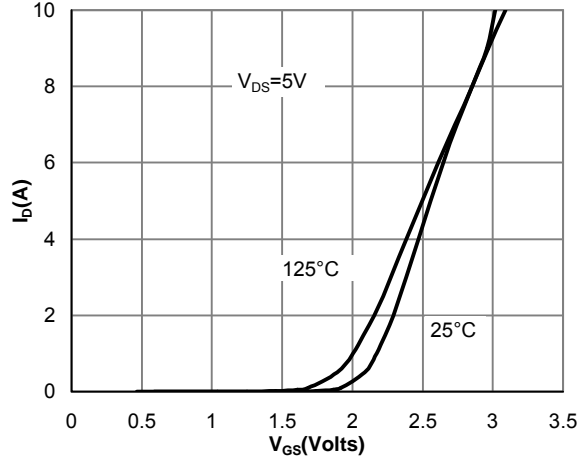


Figure 2: Transfer Characteristics

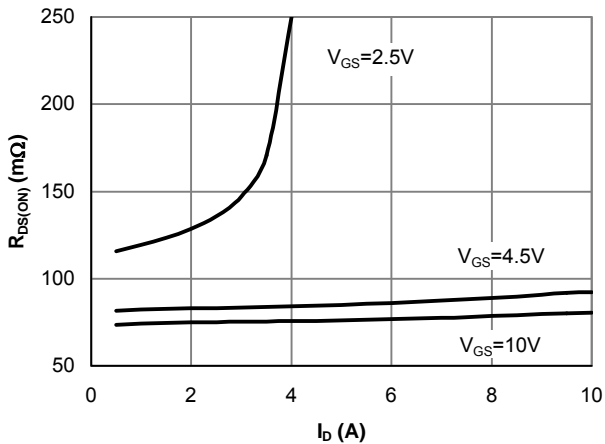


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

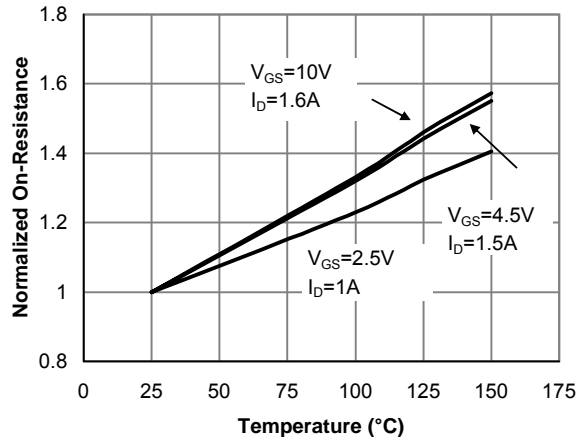


Figure 4: On-Resistance vs. Junction Temperature

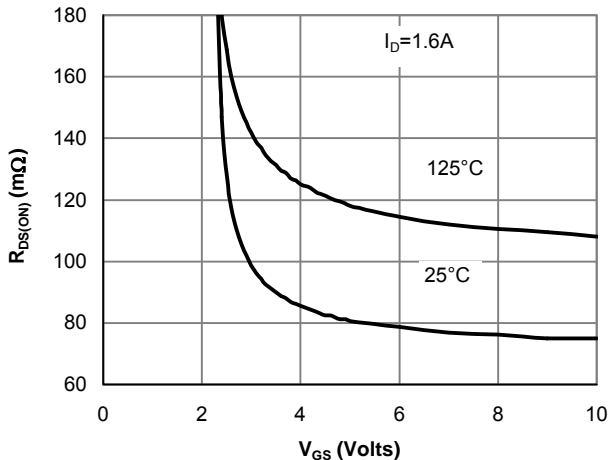


Figure 5: On-Resistance vs. Gate-Source Voltage

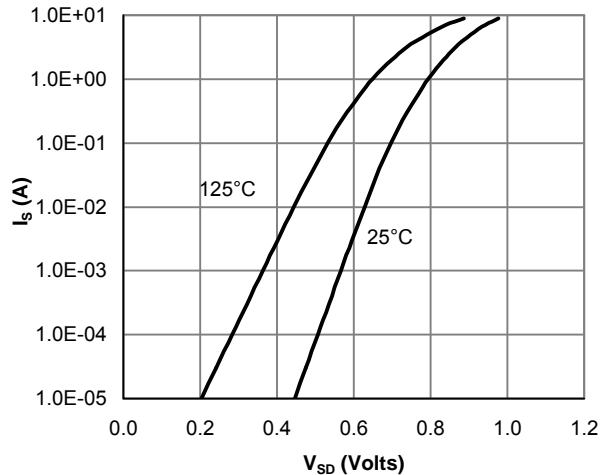


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

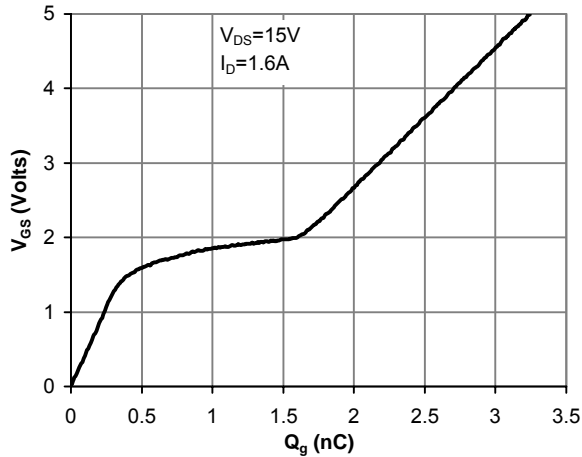


Figure 7: Gate-Charge Characteristics

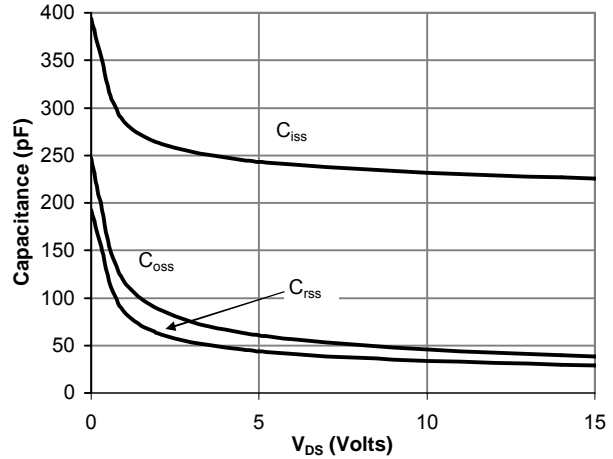


Figure 8: Capacitance Characteristics

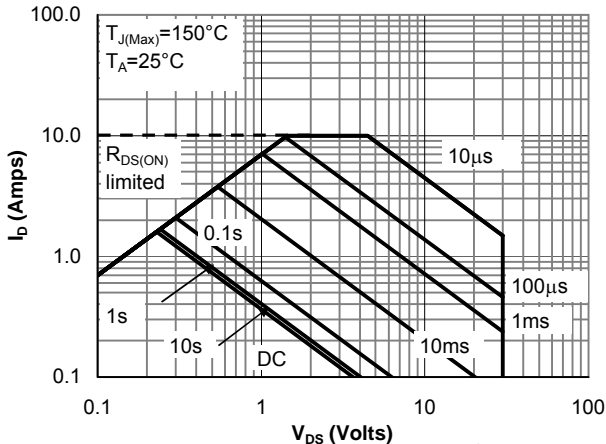


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

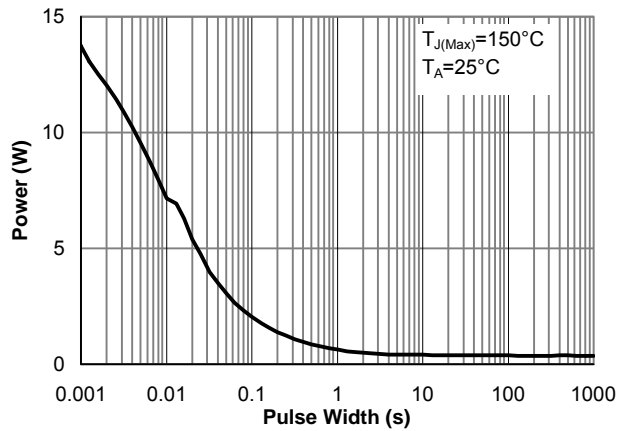


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

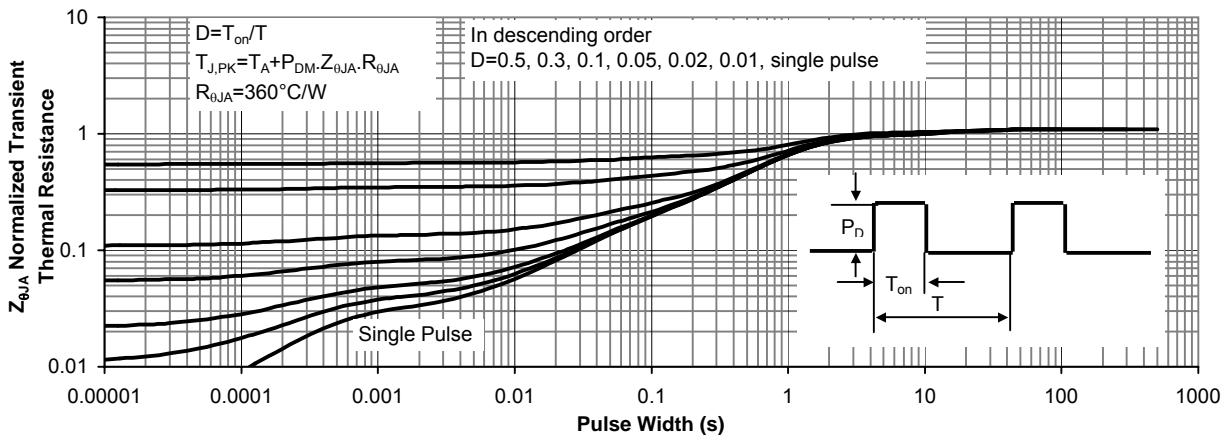


Figure 11: Normalized Maximum Transient Thermal Impedance